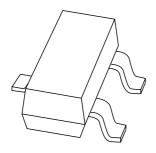
DISCRETE SEMICONDUCTORS

DATA SHEET



BCV27; BCV47 NPN Darlington transistors

Product data sheet Supersedes data of 1999 Apr 08 2004 Jan 13



NPN Darlington transistors

BCV27; **BCV47**

FEATURES

- Medium current (max. 500 mA)
- Low voltage (max. 60 V)
- High DC current gain (min. 20000).

APPLICATIONS

• Preamplifier input applications.

DESCRIPTION

NPN Darlington transistor in a SOT23 plastic package. PNP complements: BCV26 and BCV46.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCV27	FF*
BCV47	FG*

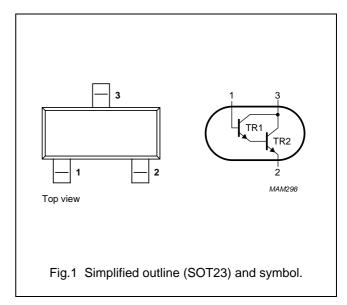
Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

TYPE	PACKAGE				
NUMBER	NAME	IE DESCRIPTION V			
BCV27	_	plastic surface mounted package; 3 leads	SOT23		
BCV47					

NPN Darlington transistors

BCV27; BCV47

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCV27		_	40	V
	BCV47		_	80	V
V _{CES}	collector-emitter voltage	open base			
	BCV27		_	30	V
	BCV47		_	60	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	800	mA
I _B	base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

^{1.} Transistor mounted on an FR4 printed-circuit board.

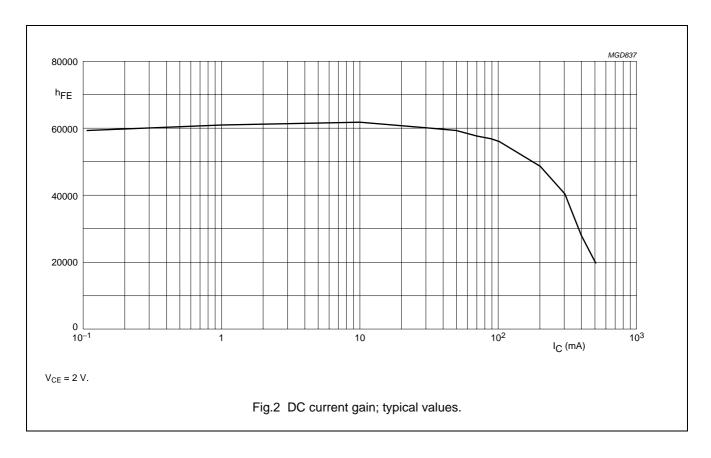
NPN Darlington transistors

BCV27; BCV47

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current					
	BCV27	I _E = 0; V _{CBO} = 30 V	_	_	100	nA
	BCV47	I _E = 0; V _{CBO} = 60 V	_	_	100	nA
I _{EBO}	emitter cut-off current	I _E = 0; V _{EB} = 10 V	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; (see Fig.2)				
	BCV27	I _C = 1 mA	4 000	_	_	
		I _C = 10 mA	10000	_	_	
		I _C = 100 mA	20000	_	_	
	DC current gain	V _{CE} = 5 V; (see Fig.2)				
	BCV47	I _C = 1 mA	2000	_	_	
		I _C = 10 mA	4 000	_	_	
		I _C = 100 mA	10000	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	_	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 100 mA; I _B = 0.1 mA	_	_	1.5	V
V _{BEon}	base-emitter on-state voltage	I _C = 10 mA; V _{CE} = 5 V	_	_	1.4	V
f _T	transition frequency	$I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	_	220	_	MHz



NPN Darlington transistors

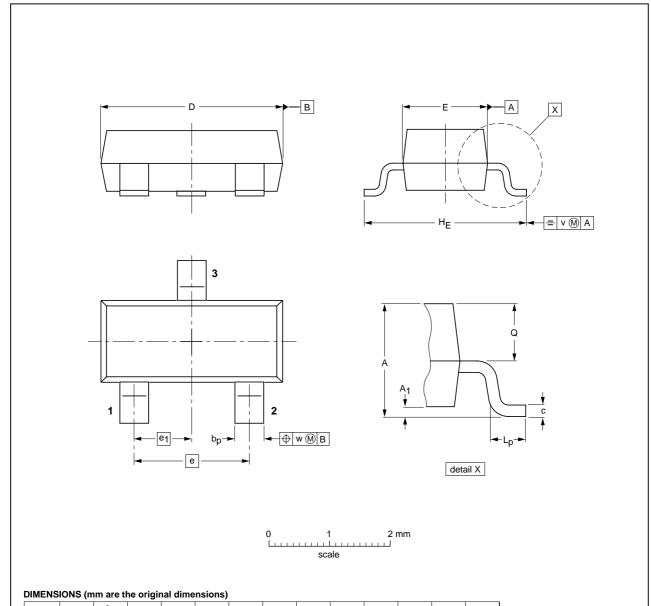
BCV27; BCV47

PACKAGE OUTLINE

UNIT

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES EUROPEAN ISSUE DA			ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE	
SOT23		TO-236AB			-04-11-04- 06-03-16	

e₁

1.9

 H_{E}

 $\mathbf{L}_{\mathbf{p}}$

0.45

0.55

0.1

2004 Jan 13 5

bp

0.38

max

0.9

NPN Darlington transistors

BCV27; BCV47

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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